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(54) **Title:** EDGE RINGS FOR IMPROVED EDGE UNIFORMITY IN SEMICONDUCTOR PROCESSING OPERATIONS

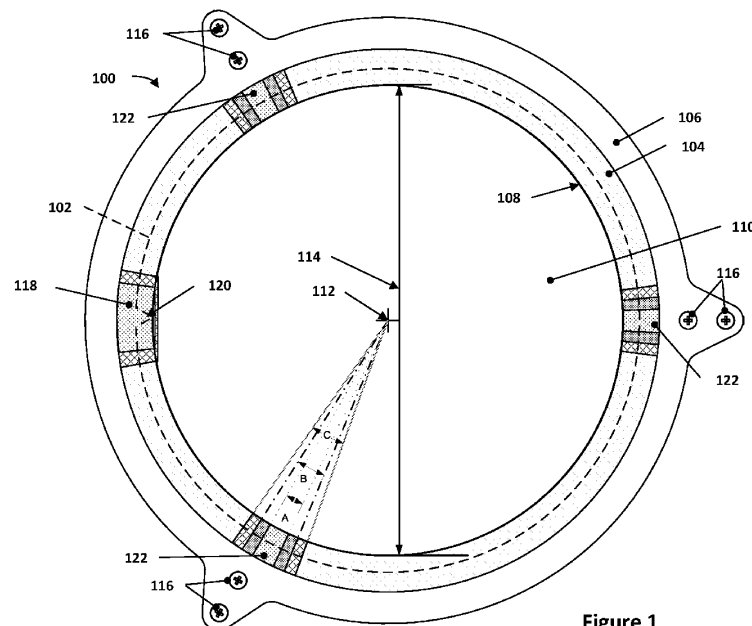


Figure 1

(57) **Abstract:** Improved edge rings with flow conductance features are disclosed. The flow conductance features of the edge ring are features added to the edge ring that adjust the flow conductance of gas flowing in the local area of the edge ring. The flow conductance features can adjust the flow conductance to compensate for features on a semiconductor wafer, the edge ring, and in the chamber that may affect the flow of gas in the local areas. The flow conductance may be increased, reduced, or tuned depending on the desired effect.

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